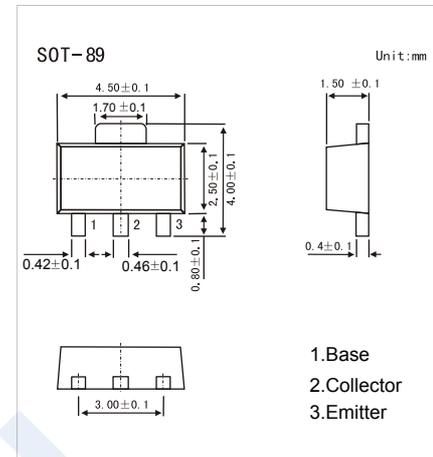


## PNP Transistors

### 2SB772A

#### ■ Features

- PNP transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SD882A



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V <sub>CB0</sub>	-70	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter to Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current to Continuous	I <sub>C</sub>	-3	A
Collector Dissipation	P <sub>c</sub>	0.5	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to 150	°C

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-70			V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> =-10 mA, I <sub>B</sub> =0	-60			V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> =-100 μA, I <sub>C</sub> =0	-6			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> =-70 V, I <sub>E</sub> =0			-1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-6V, I <sub>C</sub> =0			-1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-1A	60		400	
		V <sub>CE</sub> =-2V, I <sub>C</sub> =-100mA	32			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-2A, I <sub>B</sub> =-0.2A			-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-2A, I <sub>B</sub> =-0.2A			-1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-5 V, I <sub>C</sub> =-0.1mA, f = 10MHz	50			MHz

#### ■ Classification of h<sub>FE</sub>(1)

Type	2SB772A-R	2SB772A-Q	2SB772A-P	2SB772A-E
Range	60-120	100-200	160-320	200-400
Marking	772AR	772AQ	772AP	772AE